		Docket Number (Optional) FIS920030230US1	Application Number
INFORMATION DISCLOSURE CITATION *(Use several sheets if necessary)* OCT 0 6 2003		Applicant(s) **Bruley et al**	
		Filing Date	Group Art Unit 2814

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS   *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		American Institute of Physics, Volume 81, Number 14, September 30 2002, "Bonding States and Electrical Properties of Ultrathin HfOxNy Gate Dielectrics," Kang et al., pp. 2593-2595.
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EXAMINER	DATE CONSIDERED 7/22/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*EXAMINER INITIAL		OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*
		2002 American Institute of Physics, Volume 80, Number 17, April 29, 2002, "Application of HfSiON as a Gate Dielectric Material," Visokay et al., pp. 3183-3185.
		Journal of the Korean Physical Society, Volume 37, Number 6, December 2000, "Electrical Characteristics of AlOxNy Prepared by Oxidation of Sub-10-nm-thick AlN Films for MOS Gate Dielectric Applications," Jeon et al., pp. 886-888.
		IEEE PUBADDR, Piscataway, NJ, 1998 International Conference on Ion Implantation Technology, Ion Implantation Technology, Volume 2, June 1998, "Silicon-Aluminum Oxynitride Composite Films Deposited by Reactive Ion Beam Sputtering," Ogawa et al., pp. 775-778.
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Title of Invention	CAPACITOR AND FABRICATION METHOD USING ULTRA-HIGH VACUUM CVD OF SILICON NITRIDE

Application Number :

Confirmation Number:

First Named Applicant: John Bruley

Attorney Docket Number: FIS920030230US1

Art Unit:

Examiner:

Search string: (5943560 or 5540785 or 5462883).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5943560	1999-08-24	Chang, et al.			
	2	5540785	1996-07-30	Dennard, et al.			
	3	5462883	1995-10-31	Dennard, et al.			

Signature

Examiner Name	Date
	7/22/04